Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

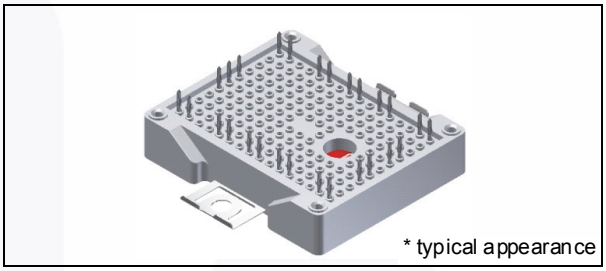
Nov. 2016

FPF2C110BI07AS2

F2, Boost and Inverter module with Press-fit

General Description

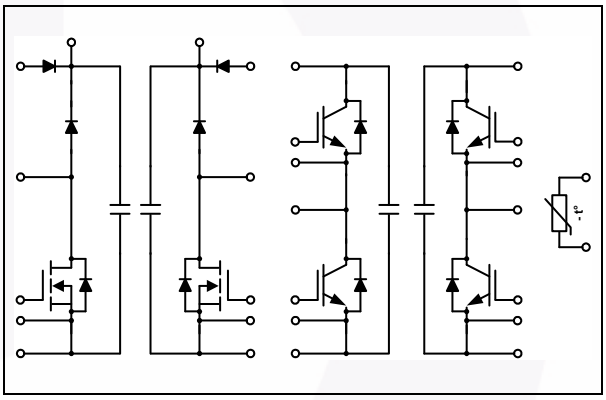
Fairchild's Boost and H-Bridge module is designed for a power stage that needs more compact design. And the Press-fit technology provides simple and reliable mounting. This module is optimized for the application such as solar inverter where a high efficiency and robust design are needed.



Package Code: F2

Electrical Features

- Boost Stage
  - Dual Boost Topology
  - SiC Boost Diode
  - Low $R_{DS(ON)}$ Boost Switch
  - Low V_F and High Voltage Bypass Diode
- Inverter Stage
  - H-bridge Topology
  - High Speed IGBT and Fast Recovery FWD
- Integrated DC-capacitor for Boost and Inverter
- Temperature Sensor



Internal Circuit Diagram

Mechanical Features

- Compact size : F2 Package
- Press-fit Contact Technology
- Al_2O_3 Substrate with Low Thermal Resistance

Applications

- Solar Inverter

Package Marking and Ordering Information

Device	Device Marking	Package	Packing Type	Quantity / Tray
FPF2C110BI07AS2	FPF2C110BI07AS2	F2	Tray	14

Absolute Maximum Ratings $T_C = 25^oC$ unless otherwise noted.

Symbol	Description	Condition	Rating	Units
Bypass Diode (DA1, DA2)				
V_{RRM}	Peak Repetitive Reverse Voltage		1000	V
I_F	Continuous Forward Current	T_C = 80 °C, T_{Jmax} = 175 °C	50	A
I_{FSM}	Non-repetitive Peak Surge Current	60 Hz Single Half-Sine Wave	350	A
I^2t	Surge Current Integral Value		510	A^2s
P_D	Maximum Power Dissipation	T_{Jmax} = 175 °C	300	W
T_J	Operating Junction Temperature		- 40 to + 150	°C
Boost Diode (DB1, DB2)				
V_{RRM}	Peak Repetitive Reverse Voltage		650	V
I_F	Continuous Forward Current	T_C = 80 °C, T_{Jmax} = 175 °C	10	A
I_{FSM}	Non-repetitive Peak Surge Current	60 Hz Single Half-Sine Wave	40	A
I^2t	Surge Current Integral Value		6.6	A^2s
P_D	Maximum Power Dissipation	T_{Jmax} = 175 °C	90	W
T_J	Operating Junction Temperature		- 40 to + 150	°C
Boost MOSFET (M1, M2)				
V_{DSS}	Drain-Source Voltage		650	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Drain Current	T_C = 25 °C, T_{Jmax} = 150 °C	25	A
		T_C = 80 °C, T_{Jmax} = 150 °C	19	A
I_{DM}	Pulsed Drain Current	limited by T_{Jmax}	50	A
P_D	Maximum Power Dissipation	T_{Jmax} = 150 °C	199	W
T_J	Operating Junction Temperature		- 40 to + 150	°C
H-bridge IGBT (QA, QB, QC, QD)				
V_{CES}	Collector-Emitter Voltage		650	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Collector Current	T_C = 80 °C, T_{Jmax} = 175 °C	40	A
I_{CM}	Pulsed Collector Current	limited by T_{Jmax}	80	A
P_D	Maximum Power Dissipation	T_{Jmax} = 175 °C	158	W
T_J	Operating Junction Temperature		- 40 to + 150	°C
H-bridge FWD (QAD, QBD, QCD, QDD)				
V_{RRM}	Peak Repetitive Reverse Voltage		650	V
I_F	Diode Forward Current	T_C = 80 °C, T_{Jmax} = 175 °C	30	A
I_{FM}	Pulsed Maximum Forward Currents	limited by T_{Jmax}	60	A
P_D	Maximum Power Dissipation	T_{Jmax} = 175 °C	109	W
T_J	Operating Junction Temperature		- 40 to + 150	°C
DC Link Capacitor				
V_{MAX}	Maximum DC Voltage		1000	V
T_{OP}	Operating Temperature		- 55 to + 125	°C

Absolute Maximum Ratings $T_C = 25^oC$ unless otherwise noted.

Symbol	Description	Condition	Rating	Units
Module				
T_{STG}	Storage Temperature		- 40 to + 125	°C
V_{ISO}	Isolation Voltage	AC 1 min.	2500	V
Iso._Material	Internal Isolation Material		Al_2O_3	-
T_{MOUNT}	Mounting Torque$_{(1)}$		2.4	N•m
Creepage	Terminal to Heat Sink		11.5	mm
	Terminal to Terminal		6.3	mm
Clearance	Terminal to Heat Sink		10.0	mm
	Terminal to Terminal		5.0	mm

Notes:

1. Recommendable value : 2.0 ~ 2.4 Nm (M4)

Electrical Characteristics T_C = 25 °C unless otherwise noted. **Parantheses value is based on the discrete.**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
Bypass Diode (DA1, DA2)						
V_F	Diode Forward Voltage	I_F = 50 A	-	1.37	1.7	V
		I_F = 50 A, T_C = 125 °C	-	1.3	-	V
I_R	Reverse Leakage Current	V_R = 1000 V	-	-	250	μA
$R_{\theta JC}$	Thermal Resistance of Junction to Case	per Diode	-	-	0.49	°C/W
$R_{\theta CH}$	Thermal Resistance of Case to Heat sink	per Chip, λ_{PCM} = 3.4 W/mK	-	0.56	-	°C/W
Boost Diode (DB1, DB2)						
V_F	Diode Forward Voltage	I_F = 10 A	-	1.42	1.58	V
		I_F = 10 A, T_C = 125 °C	-	1.61	-	V
I_R	Reverse Leakage Current	V_R = 650 V	-	-	250	μA
I_{rr}	Reverse Recovery Current	V_R = 300 V, I_F = 10 A, di / dt = 1560 A/us, T_C = 25 °C	-	6	-	A
Q_C	Total Capacitive Charge		-	60	-	nC
E_{rec}	Reverse Recovery Energy		-	7.5	-	μJ
I_{rr}	Reverse Recovery Current	V_R = 300 V, I_F = 10 A, di / dt = 1560 A/us, T_C = 125 °C	-	6	-	A
Q_C	Total Capacitive Charge		-	61	-	nC
E_{rec}	Reverse Recovery Energy		-	7.5	-	μJ
$R_{\theta JC}$	Thermal Resistance of Junction to Case	per Chip	-	-	1.63	°C/W
$R_{\theta CH}$	Thermal Resistance of Case to Heat sink	per Chip, λ_{PCM} = 3.4 W/mK	-	0.42	-	°C/W
Boost MOSFET (M1, M2)						
Off Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA	650	-	-	V
I_{DSS}	Drain Cut-off Current	V_{DS} = V_{DSS}, V_{GS} = 0 V	-	-	250	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS} = V_{GSS}, V_{DS} = 0 V	-	-	± 1	μA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250uA	3.0	3.9	5.0	V
$R_{DS(ON)}$	Static Drain-Source On Resistance	I_D = 17.5 A, V_{GS} = 10 V	-	110	137	mΩ
V_{SD}	Drain-Source Diode Forward Voltage	I_{SD} = 17.5 A, V_{GS} = 0 V	-	1.07	1.37	V
		I_{SD} = 17.5 A, V_{GS} = 0 V, T_C = 125 °C	-	0.93	-	V
R_{LEAD}	Lead Resistance of Pin to Chip	per Chip	-	3.2	-	mΩ
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 300 V, I_D = 17.5 A, V_{GS} = 10 V, R_G = 4.7 Ω, Inductive Load, T_C = 25 °C	-	27	-	ns
t_r	Rise Time		-	5.0	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	3.0	-	ns
t_f	Fall Time		-	5.5	-	ns
E_{ON}	Turn-On Switching Loss per Pulse		-	33	-	μJ
E_{OFF}	Turn-Off Switching Loss per Pulse		-	20	-	μJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 300 V, I_D = 17.5 A, V_{GS} = 10 V, R_G = 4.7 Ω, Inductive Load, T_C = 125 °C	-	26	-	ns
t_r	Rise Time		-	5.3	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	87	-	ns
t_f	Fall Time		-	6.0	-	ns
E_{ON}	Turn-On Switching Loss per Pulse		-	39	-	μJ
E_{OFF}	Turn-Off Switching Loss per Pulse		-	21	-	μJ
Q_g	Total Gate Charge	V_{CC} = 300 V, I_{SD} = 17.5 A, V_{GS} = 10 V	-	84	-	nC
$R_{\theta JC}$	Thermal Resistance of Junction to Case	per Chip	-	-	0.63	°C/W
$R_{\theta CH}$	Thermal Resistance of Case to Heat sink	per Chip, λ_{PCM} = 3.4 W/mK	-	0.49	-	°C/W

Electrical Characteristics T_C = 25 °C unless otherwise noted. **Parantheses value is based on the discrete.**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
H-Bridge IGBT (QA, QB, QC, QD)						
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	V_{GE} = 0 V, I_C = 1 mA	650	-	-	V
I_{CES}	Collector Cut-off Current	V_{CE} = V_{CES}, V_{GE} = 0 V	-	-	250	μA
I_{GES}	Gate-Emitter Leakage Current	V_{GE} = V_{GES}, V_{CE} = 0 V	-	-	± 2	μA
On Characteristics						
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	V_{GE} = V_{CE}, I_C = 40 mA	3.0	5.2	6.1	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 40 A, V_{GE} = 15 V	-	1.6	2.3	V
		I_C = 40 A, V_{GE} = 15 V, T_C = 125 °C	-	1.8	-	V
R_{LEAD}	Lead Resistance of Pin to Chip	per Chip	-	3.5	-	mΩ
Switching Characteristics (QB-QAD / QD-QCD)						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 300 V I_C = 40 A V_{GE} = 15 V R_G = 15 Ω Inductive Load T_C = 25 °C	-	26	-	ns
t_r	Rise Time		-	22	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	125	-	ns
t_f	Fall Time		-	14	-	ns
E_{ON}	Turn-On Switching Loss per Pulse		-	0.45	-	mJ
E_{OFF}	Turn-Off Switching Loss per Pulse		-	0.27	-	mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 300 V I_C = 40 A V_{GE} = 15 V R_G = 15 Ω Inductive Load T_C = 125 °C	-	24	-	ns
t_r	Rise Time		-	25	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	139	-	ns
t_f	Fall Time		-	13	-	ns
E_{ON}	Turn-On Switching Loss per Pulse		-	0.74	-	mJ
E_{OFF}	Turn-Off Switching Loss per Pulse		-	0.35	-	mJ
Q_g	Total Gate Charge	V_{CC} = 300 V, I_C = 40 A, V_{GE} = 15 V	-	60	-	nC
$R_{\theta JC}$	Thermal Resistance of Junction to Case	per Chip	-	-	0.95	°C/W
$R_{\theta CH}$	Thermal Resistance of Case to Heat sink	per Chip, λ_{PCM} = 3.4 W/mK	-	0.64	-	°C/W
H-bridge FWD (QAD, QBD, QCD, QDD)						
V_F	Diode Forward Voltage	I_F = 30 A	-	2.45	3.2	V
		I_F = 30 A, T_C = 125 °C	-	2.15	-	V
I_R	Reverse Leakage Current	V_R = 650 V	-	-	250	μA
I_{rr}	Reverse Recovery Current	V_R = 300 V, I_F = 30 A, di / dt = 1570 A/us, T_C = 25 °C	-	20.1	-	A
t_{rr}	Reverse Recovery Time		-	30	-	ns
E_{rec}	Reverse Recovery Energy		-	27	-	μJ
I_{rr}	Reverse Recovery Current	V_R = 300 V, I_F = 30 A, di / dt = 1135 A/us, T_C = 125 °C	-	23.1	-	A
t_{rr}	Reverse Recovery Time		-	52	-	ns
E_{rec}	Reverse Recovery Energy		-	73	-	μJ
$R_{\theta JC}$	Thermal Resistance of Junction to Case	per Chip	-	-	1.38	°C/W
$R_{\theta CH}$	Thermal Resistance of Case to Heat sink	per Chip, λ_{PCM} = 3.4 W/mK	-	0.45	-	°C/W
DC link Capacitor						
C value	Capacitance Value		-	47	-	nF
NTC (Thermistor)						
R_{NTC}	Rated Resistance	T_C = 25 °C	-	22	-	kΩ
		T_C = 100 °C	-	1.486	-	kΩ
	Tolerance	T_C = 25 °C	-5	-	+5	%
P_D	Power Dissipation	T_C = 25 °C	-	-	20	mW
B_{Value}	B-Constance	$B_{25/50}$, tol.	-	3950	-	K
		$B_{25/100}$	-	3998	-	K

Typical Performance Characteristics

Fig 1. Forward Voltage Drop - Bypass Diode

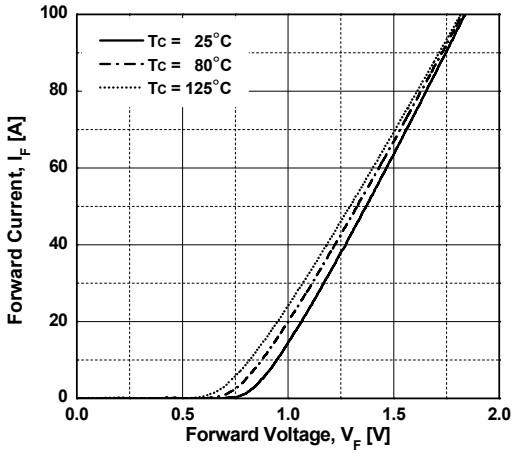


Fig 2. Transient Thermal Impedance - Bypass Diode

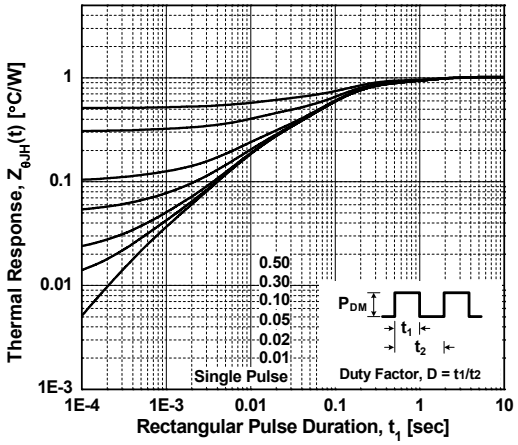


Fig 3. Forward Voltage Drop - Boost Diode

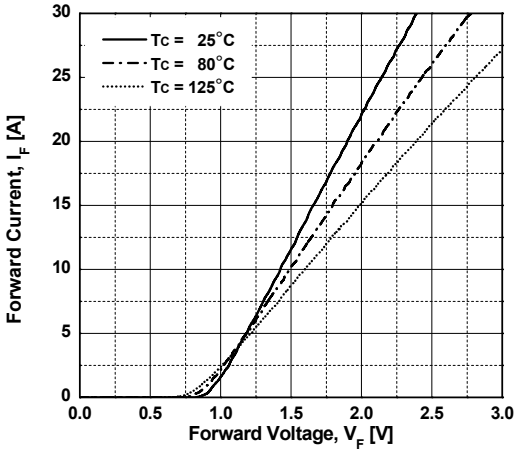


Fig 4. Transient Thermal Impedance - Boost Diode

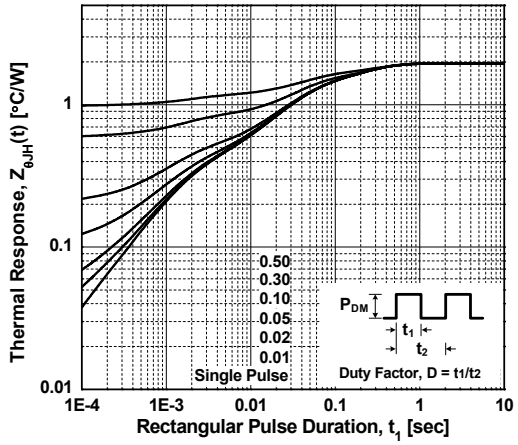


Fig 5. On-Region Characteristics - Boost MOSFET

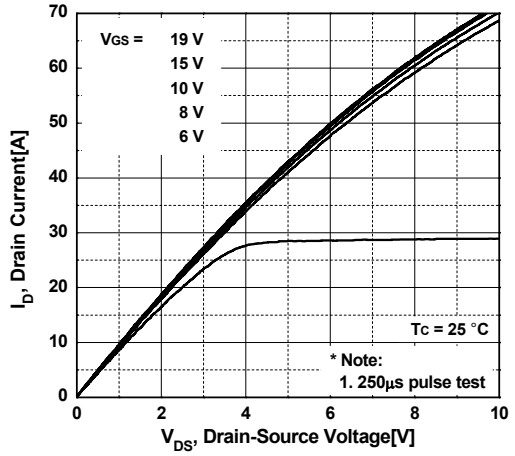
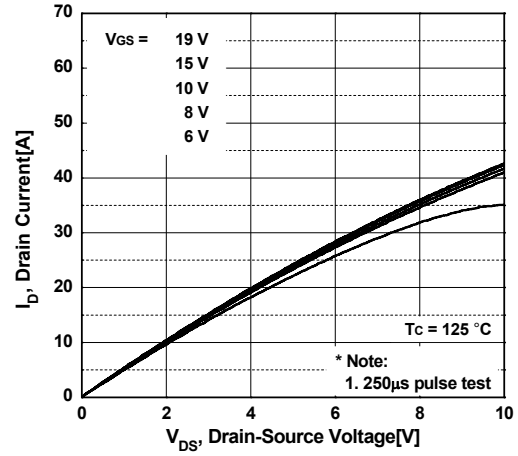


Fig 6. On-Region Characteristics - Boost MOSFET



Typical Performance Characteristics

Fig 7. On-Resistance Variation vs. Temperature - Boost MOSFET

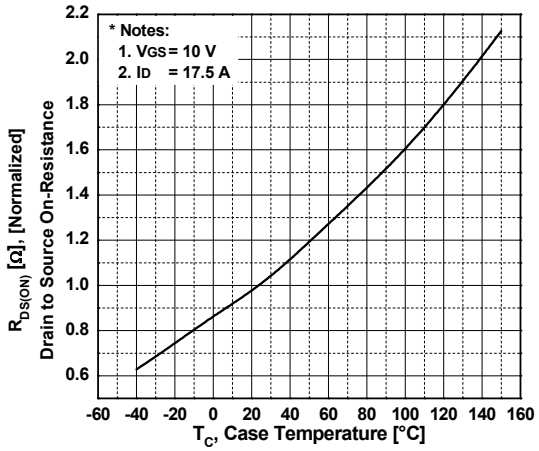


Fig 8. Switching Loss vs. Gate Resistor Values - Boost MOSFET

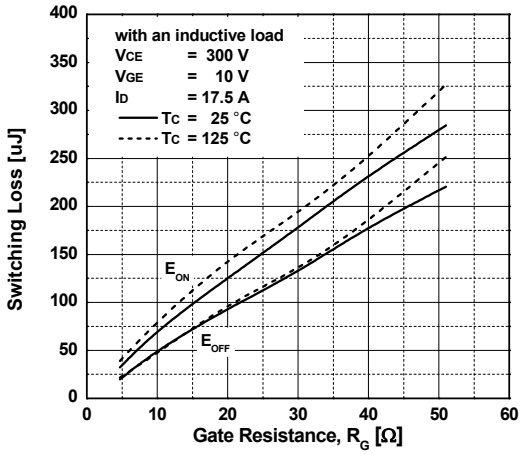


Fig 9. Switching Loss vs. Drain Current - Boost MOSFET

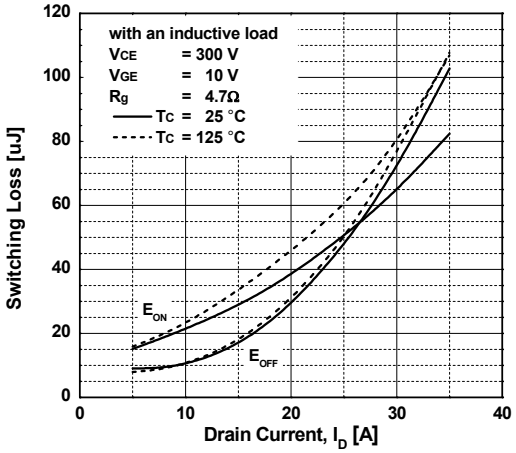


Fig 10. Body Diode Forward Voltage Variation vs. Source Current and Temperature - Boost MOSFET

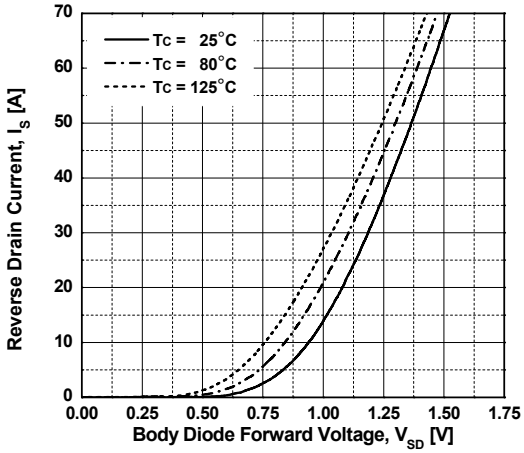


Fig 11. Transient Thermal Impedance - Boost MOSFET

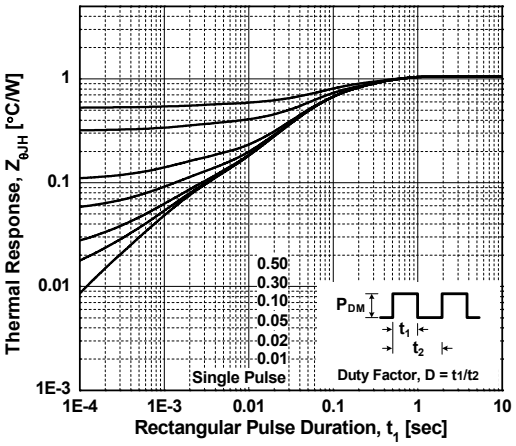
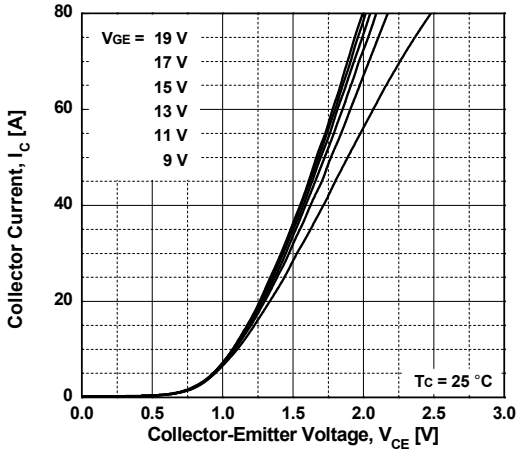


Fig 12. Output Characteristics - H-bridge IGBT



Typical Performance Characteristics

Fig 13. Output Characteristics - H-bridge IGBT

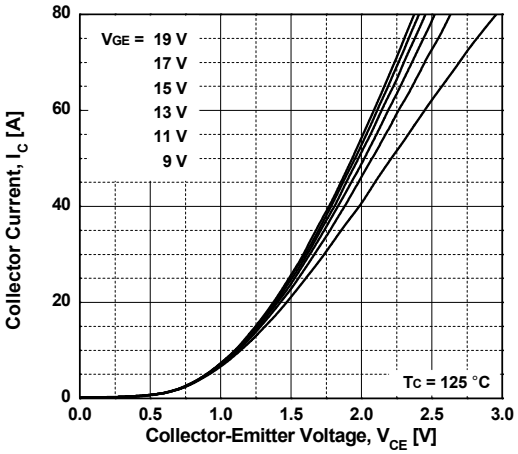


Fig 14. Saturation Voltage Characteristics - H-bridge IGBT

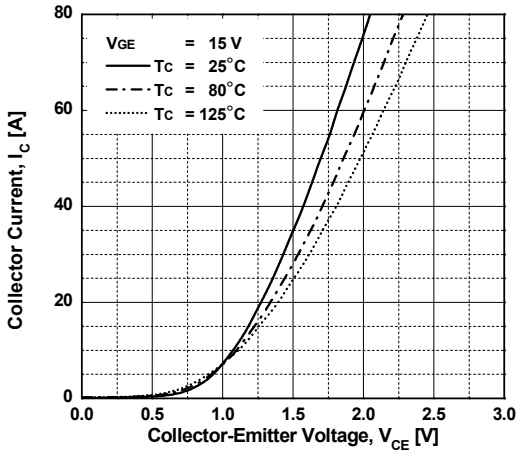


Fig 15. Switching Loss vs. Gate Resistor Values - H-bridge IGBT

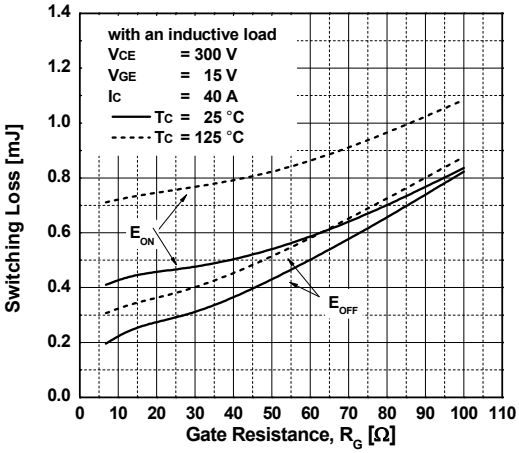


Fig 16. Switching Loss vs. Collector Current - H-bridge IGBT

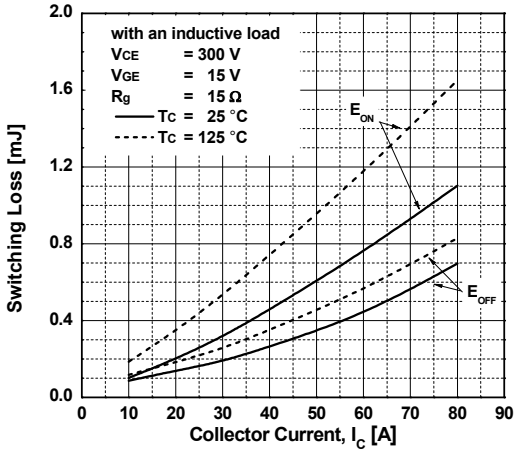


Fig 17. Transient Thermal Impedance - H-bridge IGBT

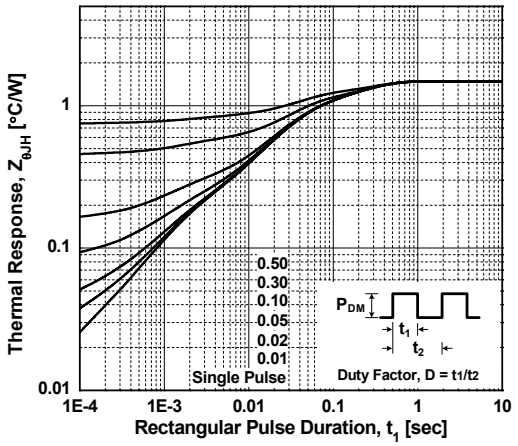
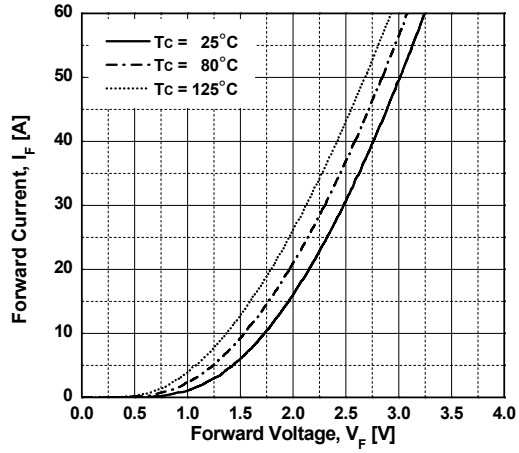


Fig 18. Forward Voltage Drop vs. Forward Current - H-bridge FWD



Typical Performance Characteristics

Fig 19. Reverse Recovery Energy vs. Gate Resistor Values - H-bridge FWD

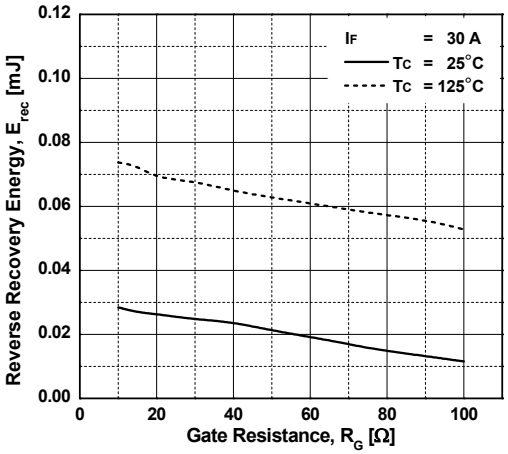


Fig 20. Reverse Recovery Energy vs. Forward Current - H-bridge FWD

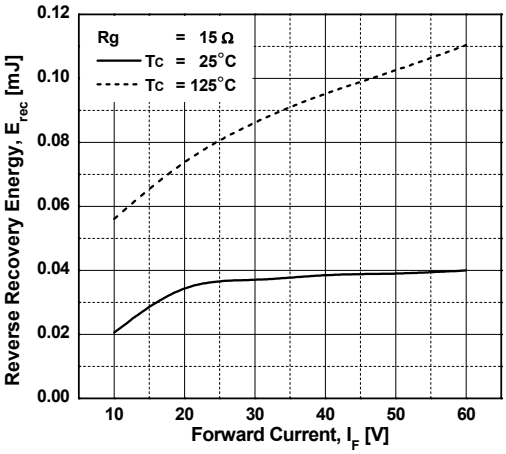
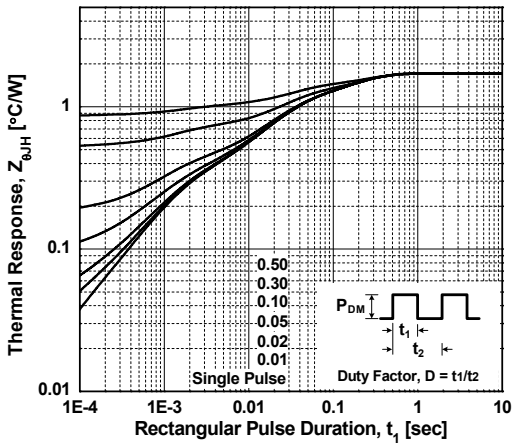
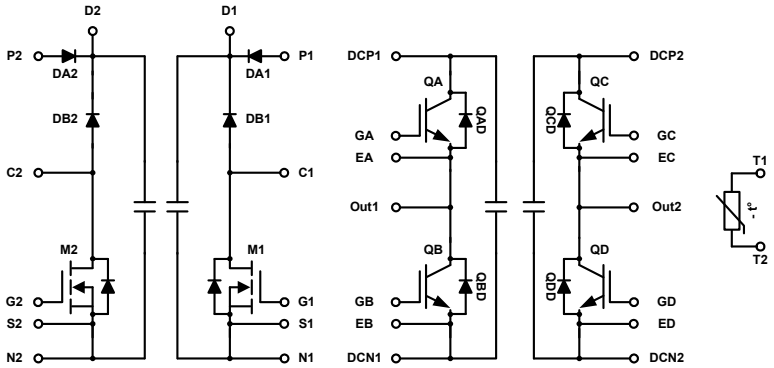


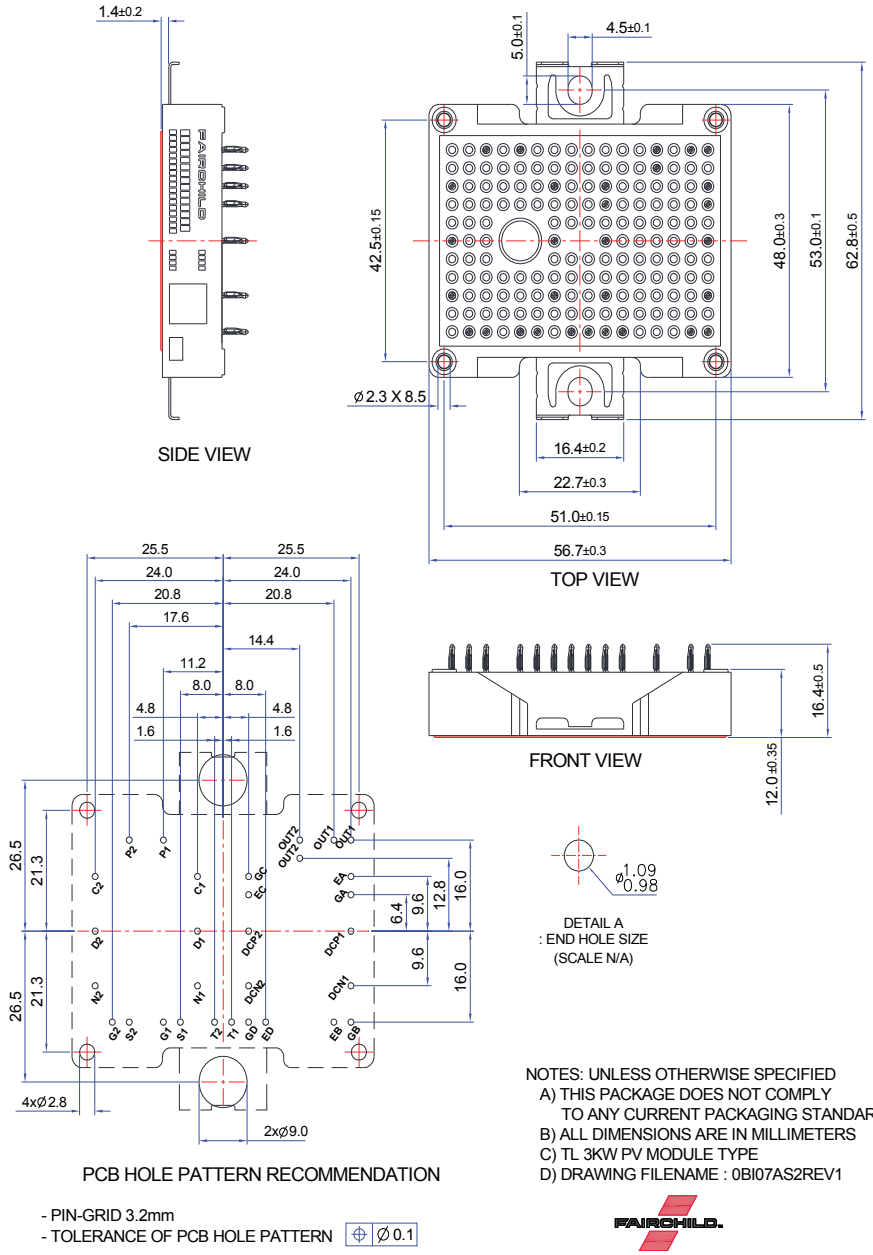
Fig 21. Transient Thermal Impedance - H-bridge FWD



Internal Circuit Diagram



Package Outlines [mm]



- PIN-GRID 3.2mm
- TOLERANCE OF PCB HOLE PATTERN ⌖ | Ø 0.1

NOTES: UNLESS OTHERWISE SPECIFIED
A) THIS PACKAGE DOES NOT COMPLY TO ANY CURRENT PACKAGING STANDARD
B) ALL DIMENSIONS ARE IN MILLIMETERS
C) TL 3KW PV MODULE TYPE
D) DRAWING FILENAME : 0BI07AS2REV1

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™
AttitudeEngine™
Awinda®
AX-CAP®*
BitSiC™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficientMax™
ESBC™
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FastvCore™
FETBench™
FPS™
F-PFS™
FRFET®
Global Power Resource SM
GreenBridge™
Green FPS™
Green FPS™ e-Series™
G*max*™
GTO™
IntelliMAX™
ISOPLANAR™
Making Small Speakers Sound Louder and Better™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
MotionGrid®
MTi®
MTx®
MVN®
mWSaver®
OptoHiT™
OPTOLOGIC®
OPTOPLANAR®
Power Supply WebDesigner™
PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
Saving our world, 1mW/W/kW at a time™
SignalWise™
SmartMax™
SMART START™
Solutions for Your Success™
SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™
SYSTEM GENERAL®*
TinyBoost®
TinyBuck®
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TranSiC™
TriFault Detect™
TRUECURRENT®*
μSerDes™
SerDes
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™
Xsens™
仙童®

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT HTTP://WWW.FAIRCHILDSEMI.COM. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

AUTHORIZED USE

Unless otherwise specified in this data sheet, this product is a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability. This product may not be used in the following applications, unless specifically approved in writing by a Fairchild officer: (1) automotive or other transportation, (2) military/aerospace, (3) any safety critical application – including life critical medical equipment – where the failure of the Fairchild product reasonably would be expected to result in personal injury, death or property damage. Customer's use of this product is subject to agreement of this Authorized Use policy. In the event of an unauthorized use of Fairchild's product, Fairchild accepts no liability in the event of product failure. In other respects, this product shall be subject to Fairchild's Worldwide Terms and Conditions of Sale, unless a separate agreement has been signed by both Parties.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Terms of Use

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I77

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor:

FPF2C110BI07AS2

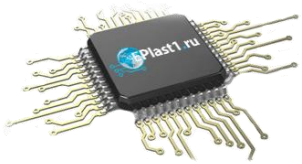
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)
Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.